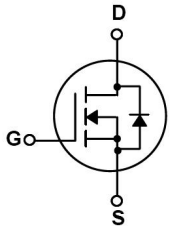
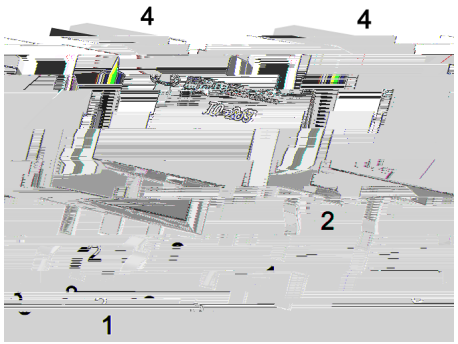
TO-263 ḾḾḪ N ʚ ɟ ѽ Ƶ ᒣ
N-CHANNEL MOSFET in a TO-263 Plastic Package.

Ꮋ ɔ ڳ/Ầ ʜ ѧ ẙ ồ ı ᒣ ᵀ DHF0T434 ‰´ ᴤ ᶦ ˎ ό ɭ ∂ ı ṇ ꜰ ᵝ
Xowud Orz Rq0Uhvlvwdqfh/idvw vzlwfklqj/ Txdolilhg wr DHF0T434 Vwdqgdugv iru Klj k Uholdelolw|/ KI Surgxfw1

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ǂ ɭ ∂
These devices are well suited for high efficient switched mode power supplies Active power factor correction, electronic lamp ballast based on half bridge topology, Meet the stringent requirements of automotive applications.





PIN1 χ G PIN 2 4 χ D PIN 3 χ S

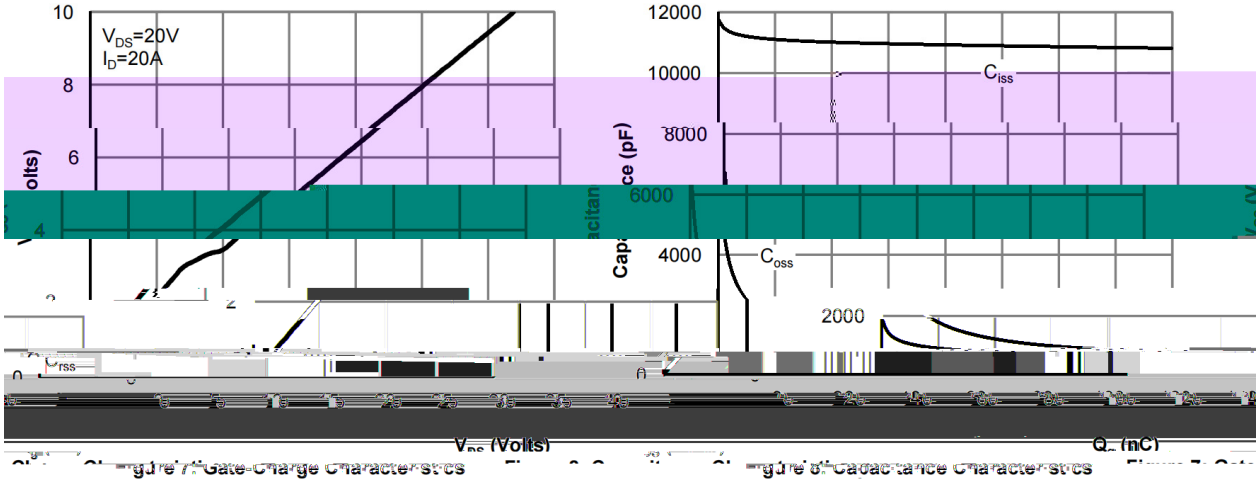
/ Marking

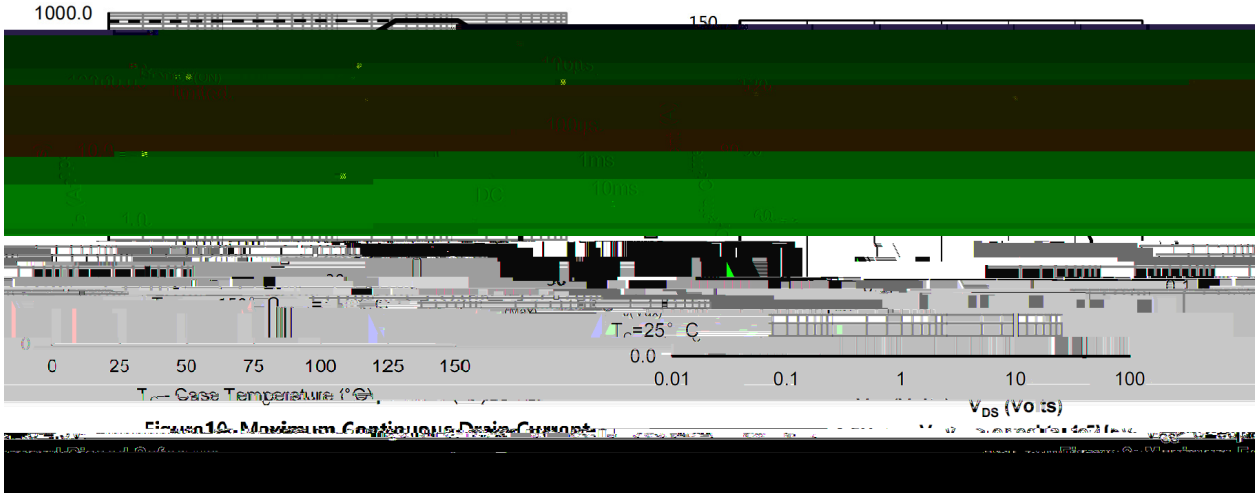
ȣ ᴍ ᒣ ب ˝ See Marking Instructions.

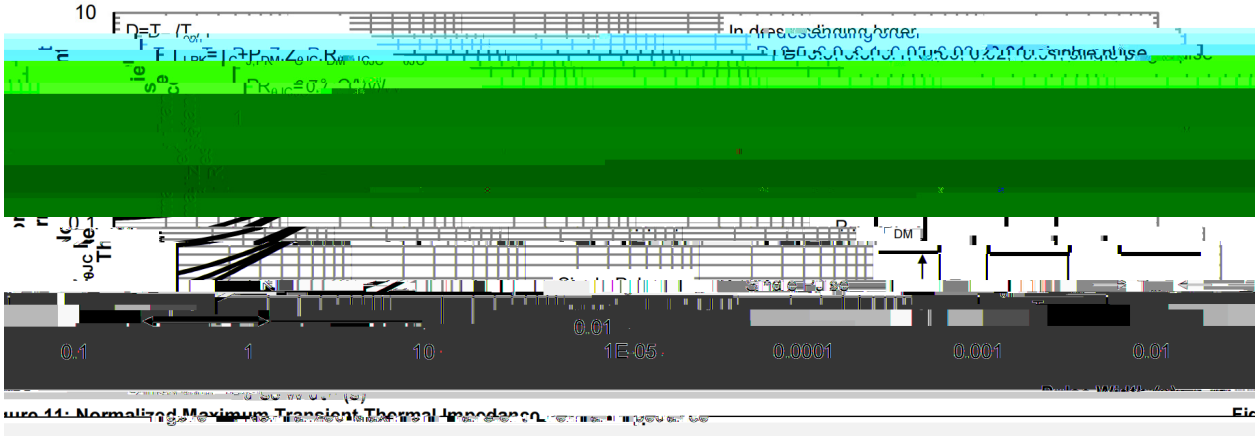
Par[illegible]er		Symbol	Rating	Unit
Dr[illegible]Source Voltage		V_{DSS}	40	V
Dr[illegible]Current		I_D(Tc=25)	120	A
Pu[illegible] Drain Current		I_{DM}	480	A
Ga[illegible]urce Voltage		V_{GS}	±20	V
Sing[illegible]ed Avalanche E[illegible]		E_{AS}	482	mJ
Avala[illegible]urrent		I_{AS}	35	A
Total Power Dissipation		P_D(Tc=25)	187	W
Junction and Storage Temperature Range		T_J,T_{STG}	-55 to 175	
T[illegible]Resistance-Junction t[illegible]	t ≤ 10s	$R_{\theta JA}$	15	℃/W
	Steady-State		60	
Thermal [illegible]unction to Case	Steady-State	$R_{\theta JC}$	0.7	

Pa[illegible]eter		Test Conditions		Min	Typ	Max	Unit
Drain-Source [illegible]kdo[illegible]	BV_{DSS}	V_{GS}=0V	I_D=250μA	40	44		V
Zero Gate Vo[illegible]rrent	I_{DSS}	V_{DS}=40V	V_{GS}=0V			1	μA
Gate-Bo[illegible]Current Fo[illegible]	I_{GSS}	V_{GS}=±20V	V_{DS}=0V			±1[illegible]	nA
[illegible]eshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}	I_D=250μA	1	1[illegible]	3	V
Static Drain-Source I							

/ Electrical Characteristic Curve







/ Package Dimensions

